

Session Title:	56. Emerging Devices for Display
Session Date:	August 22 (Fri.), 2025
Session Time:	11:00-12:50
Session Room:	Room H (316~317)
Session Chair(s):	Dr. SooJi Nam (ETRI, Korea) Prof. Soong Ju Oh (Korea Univ., Korea)

[H56-1] [Invited]	11:00-11:25
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Nanocrystal and Quantum Dot Based Electronic, Optoelectronic Devices and Sensors
Soong Ju Oh (Korea Univ., Korea)

[H56-2] [Invited]	11:25-11:50
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Quantum Dots for Colour Conversion on μ LEDs – Particle Systems, Stability and other Tasks
Jan S. Niehaus, Sören Becker (Center for Applied Nanotechnology GmbH, Germany), and
Armin Wedel (Fraunhofer IAP, Germany)

[H56-3]	11:50-12:05
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Interfacial Defect Effect Between Chalcogenide Ovonic Threshold Switch and Metal Electrodes
MiRiNae Lee (ETRI & Univ. of Science and Tech., Korea), Junghoon Han (ETRI & Korea Univ., Korea), ChaHwan Yang (ETRI & Univ. of Science and Tech., Korea), Kyunghee Choi (ETRI, Korea), and Sooji Nam (ETRI & Univ. of Science and Tech., Korea)

[H56-4]	12:05-12:20
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IGZO-Based Optoelectronic Dual-Mode Devices with Reduction-Engineered Blue TiO_2 Absorption Layer
Su Min Park, Kunho Moon, Kyu Min Kim, Dong Keun Lee, and Hyun Jae Kim (Yonsei Univ., Korea)

[H56-5]	12:20-12:35
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Engineering P-Type Contacts in 2D WSe_2 Transistors via Selenium Interlayers: Leveraging Fermi-Level Pinning for Enhanced Performance
Soonhyo Kim, Taoyu Zou, Seongmin Heo, Mingyu Kim, and Yong-Young Noh (POSTECH, Korea)

[H56-6]	12:35-12:50
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Strain-Engineered Highly Flexible Dual-Gate MoS_2 Thin-Film Transistor with Graphene Electrodes
Mingu Kang, Jeoungmin Ji, Seohak Park, Su-Bon Kim, Inseong Lee, Hyeongjin Lim, and Seunghyup Yoo, and Sung-Yool Choi (KAIST, Korea)